



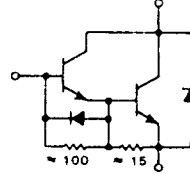
SWITCHMODE SERIES

NPN SILICON POWER DARLINGTON TRANSISTORS WITH BASE-EMITTER SPEEDUP DIODE

The MJ10024 and MJ10025 darlington transistors are designed for high-voltage, high-speed, power switching in inductive circuits where fall time is critical. They are particularly suited for line operated switchmode applications such as:

FEATURES:

- *Continuous Collector Current - $I_C = 20$ A
- *Switching Regulators
- *Inverters
- *Solenoid and Relay Drivers
- *AC and DC Motor Controls

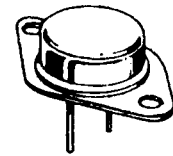


NPN
MJ10024
MJ10025

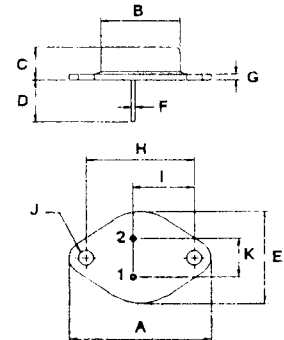
20 AMPERE
POWER DARLINGTON
TRANSISTORS
750-850 VOLTS
250 WATTS

MAXIMUM RATINGS

Characteristic	Symbol	MJ10024	MJ10025	Unit
Collector-Emitter Voltage	V_{CEV}	1000	1200	V
Collector-Emitter Voltage	$V_{CEO(SUS)}$	750	850	V
Emitter-Base Voltage	V_{EBO}	8.0		V
Collector Current-Continuous	I_C	20		A
-Peak	I_{CM}	40		A
Base current	I_B	10		A
Total Power Dissipation @ $T_C = 25^\circ C$	P_D	250		W
Derate above $25^\circ C$		143		W
		1.43		W/ $^\circ C$
Operating and Storage Junction Temperature Range	T_J, T_{STG}	- 65 to +200		$^\circ C$



TO-3

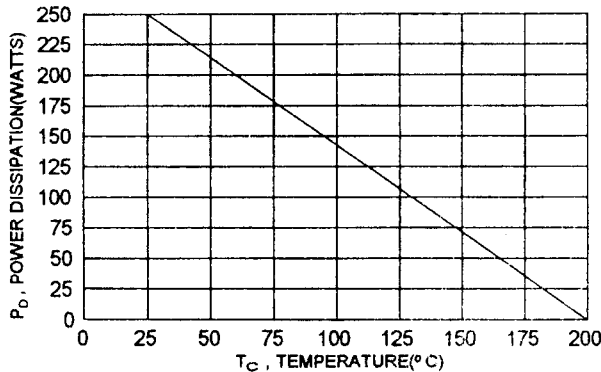


PIN 1.BASE
2.EMITTER
COLLECTOR(CASE)

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	0.7	$^\circ C/W$

FIGURE -1 POWER DERATING



DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18

ELECTRICAL CHARACTERISTICS ($T_c = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
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OFF CHARACTERISTICS

Collector - Emitter Sustaining Voltage ($I_C = 100\text{ mA}$, $I_B = 0$)	MJ10024 MJ10025	$V_{CEO(sus)}$	750 850	V
Collector Cutoff Current ($V_{CEV} = \text{Rated Value}$, $V_{BE(OFF)} = 1.5\text{ V}$) ($V_{CEV} = \text{Rated Value}$, $V_{BE(OFF)} = 1.5\text{ V}$, $T_C = 150^\circ\text{C}$)		I_{CEV}	0.25 5.0	mA
Collector Cutoff Current ($V_{CEV} = \text{Rated}$, $V_{CEV}, R_{BE} = 50\ \Omega$, $T_C = 100^\circ\text{C}$)		I_{CER}	5.0	mA
Emitter Cutoff Current ($V_{EB} = 2.0\text{ V}$, $I_C = 0$)		I_{EBO}	175	mA

ON CHARACTERISTICS (1)

DC Current Gain ($I_C = 5.0\text{ A}$, $V_{CE} = 5.0\text{ V}$)		hFE	50	600	
Collector - Emitter Saturation Voltage ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$) ($I_C = 20\text{ A}$, $I_B = 5.0\text{ A}$) ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$, $T_C = 100^\circ\text{C}$)		$V_{CE(sat)}$		2.2 5.0 2.5	V
Base - Emitter Saturation Voltage ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$) ($I_C = 10\text{ A}$, $I_B = 1.0\text{ A}$, $T_C = 100^\circ\text{C}$)		$V_{BE(sat)}$		2.5 2.5	V
Diode Forward Voltage ($I_F = 10\text{ A}$)		V_F		4.0	V

DYNAMIC CHARACTERISTICS

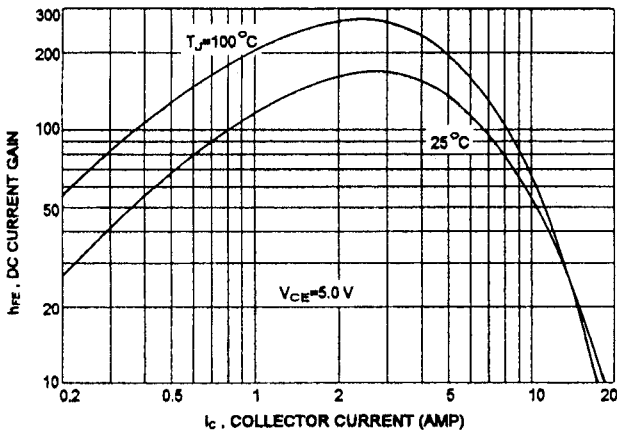
Output Capacitance ($V_{CB} = 10\text{ V}$, $I_E = 0$, $f = 1.0\text{ kHz}$)		C_{ob}	100	600	pF
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SWITCHING CHARACTERISTICS

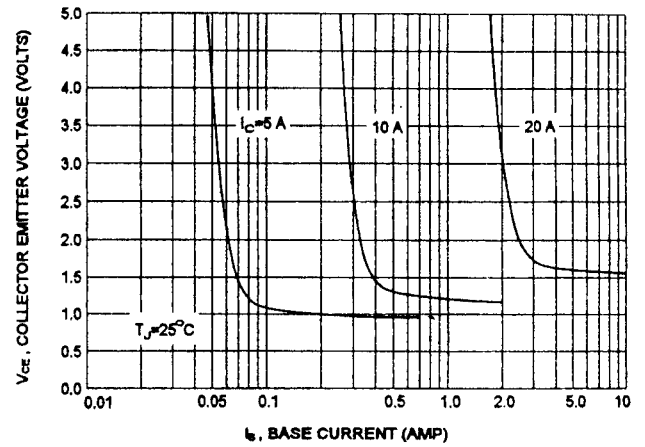
Delay Time	$V_{CC} = 250\text{ V}$, $I_C = 10\text{ A}$ $I_{B1} = 1.0\text{ A}$, $V_{BE(off)} = 5.0\text{ V}$ $t_p = 50\mu\text{s}$, Duty Cycle $\leq 2\%$	t_d		0.4	us
Rise Time		t_r		1.8	us
Storage Time		t_s		5.0	us
Fall Time		t_f		1.8	us

(1) Pulse Test: Pulse width = $300\ \mu\text{s}$, Duty Cycle $\leq 2.0\%$

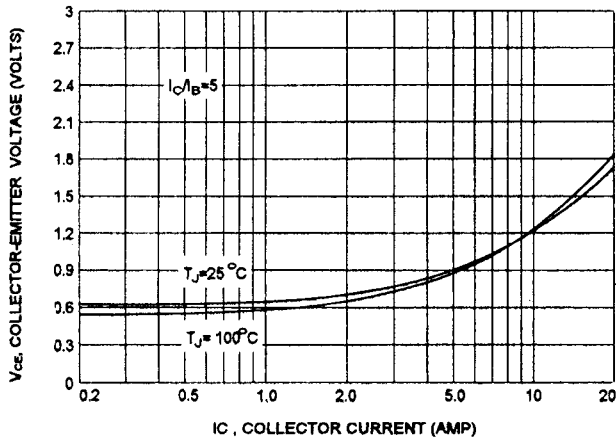
DC CURRENT GAIN



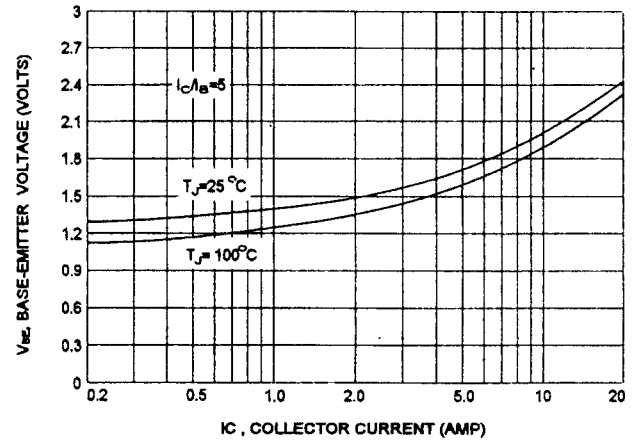
COLLECTOR SATURATION REGION



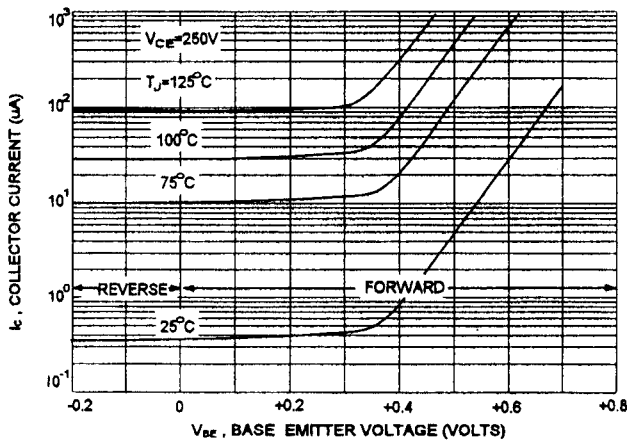
COLLECTOR-EMITTER SATURATION VOLTAGE



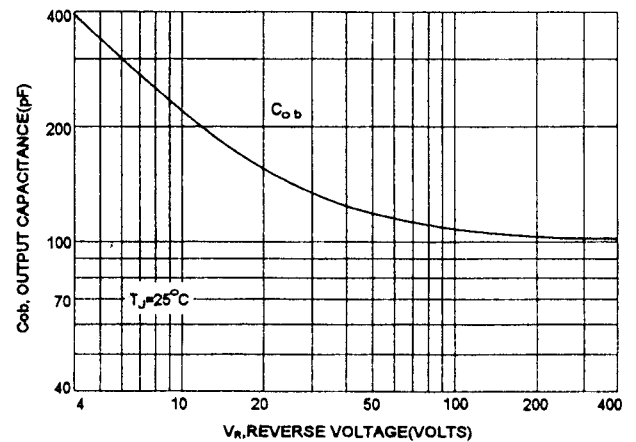
BASE-EMITTER SATURATION VOLTAGE



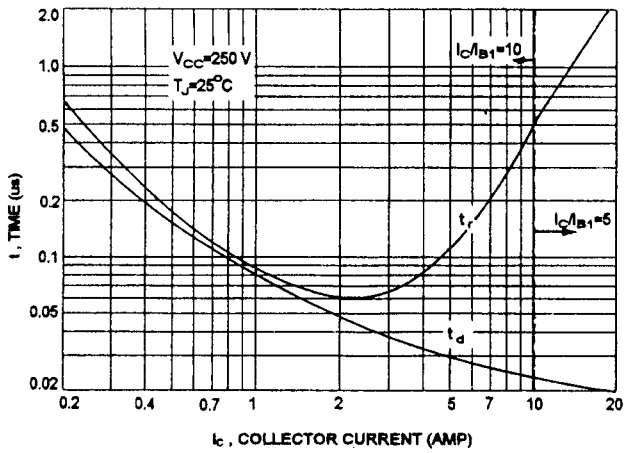
COLLECTOR CUT-OFF REGION



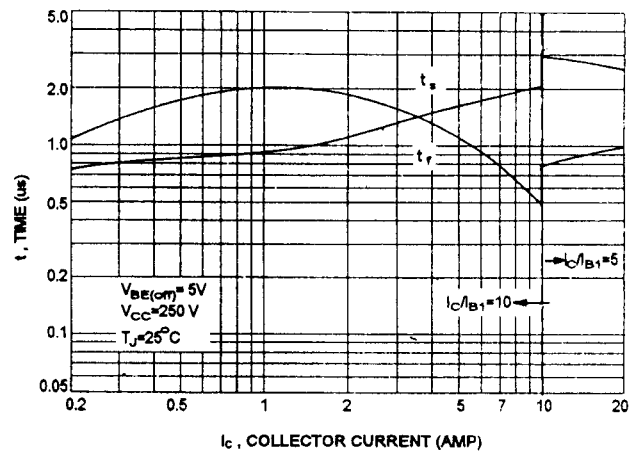
OUTPUT CAPACITANCES



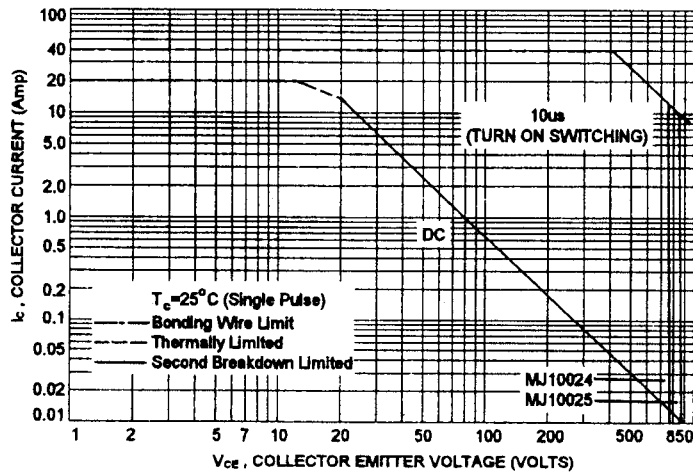
TURN-ON TIME



TURN-OFF TIME



ACTIVE REGION SAFE OPERATING AREA



REVERSE BIAS SWITCHING SAFE OPERATING AREA

